JANHCH1N5807, JANHCH1N5809, JANHCH1N5811 JANKCH1N5807, JANKCH1N5809, JANKCH1N5811

ULTRAFAST RECOVERY SILICON RECTIFIER DIE

TECHNICAL DATA DATA SHEET 6122, REV -

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FEATURES / BENEFITS:

- ✓ Die fabricated on a MIL-PRF-19500 JANKC qualified manufacturing line
- ✓ Class H and class K element evaluation per MIL-PRF-19500/477
- ✓ All ratings are @ T_A = 25 °C unless otherwise specified

ELECTRICAL CHARACTERISTICS:

Maximum Ratings:

Characteristics	Symbol	Condition	Min.	Max.	Units
Peak Inverse Voltage					
DC Blocking Voltage	V_{RWM}				
1N5807	V KVVIVI	_		50	V
1N5809				100	•
1N5811				150	
Breakdown Voltage					
1N5807	V _{BR1}	I _{BR} =100µA	60		
1N5809	V DICT	ιεκ 100μ/ τ	110		V
1N5811			160		
Max. Average Forward Current	I _{F(AV)}	T _A = 55°C		3.0	Α
Max. Peak One Cycle Non-	I _{FSM}	T_{p} = 8.3 ms		125	Α
Repetitive Surge Current		1 p= 0.5 1113			
Max. Junction Temperature	T_J	-	-65	+175	°C
Max. Storage Temperature	T_{stg}	-	-65	+175	°C

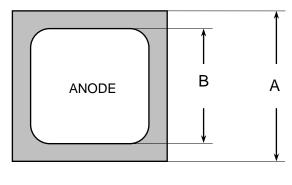
Electrical Characteristics:

Electrical Characteristics.				
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{FM3}	I _{FM} =3.0A, T _J = 25 °C	0.865	V
	V _{FM4}	I _{FM} =4.0A, T _J = 25 °C	0.875	V
	V_{FM5}	I _{FM} =6.0A, T _J = 25 °C	0.925	
	V _{FM7}	I _{FM} =4.0A, T _J = 125 °C	0.800	V
	V _{FM8}	I _{FM} =4.0A, T _J = -65 °C	1.075	V
Max. Reverse Current	I _{R1}	V _R = V _{RWM} , pulse, T _J = 25 °C	5.0	μА
	I _{R2}	V _R = V _{RWM} , pulse, T _J = 125 °C	525	μА
Breakdown Voltage 1N5807 1N5809 1N5811	V _{BR2}	I _{BR} =100uA, T _J = -65 °C	50 100 150	V
Reverse Recovery Time	t _{rr}	$I_F = I_R = 1.0A, I_{RM} = 0.1A$	30	ns
Max. Junction Capacitance	Ст	$V_R = 10V, T_C = 25 ^{\circ}C$ f = 1Mhz, $V_{SIG} = 50mV (p-p)$	60	pF

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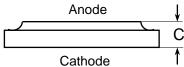
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PACKAGE DIMENSIONS (inches/mm):



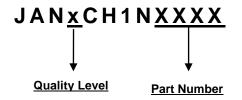
Top anode and bottom cathode

Top Metal Ti (0.3 kA) / Al (45 kA) nominal Bottom Metal Ti (1.2 kA) / Ni (1.8 kA) / Ag (3.0 kA) nominal



	Dimensions				
1.4	1N5807, 1N5809, 1N5811				
Ltr	Inc	hes	Millimeters		
	Min	Max	Min	Max	
А	.062	.068	1.57	1.73	
В	.046	.052	1.17	1.32	
С	.008	.012	0.20	0.30	

PART ORDERING INFORMATION:



Suffix	Part Number	Description
Н	JANHCH1N5807	Class H Level
K	JANKCH1N5807	Class K Level



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